Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

(Currently Amended) An electroluminescent device device, comprising:
first electrodes;

electroluminescent layers disposed over the first electrodes;

a second electrode disposed to over the electroluminescent layers; and

a barrier layer in direct contact with the second electrode,

wherein at least the surface of the second electrode facing the barrier layer comprises including an inorganic oxide, and

at least the surface of the barrier layer facing the second electrode comprises including an inorganic compound.

- 2. (Currently Amended) The electroluminescent device according to claim 1, wherein the second electrode comprises including indium tin oxide or indium zinc oxide.
- 3. (Currently Amended) The electroluminescent device according to claim 1, wherein the second electrode covers covering side faces and upper faces of the electroluminescent layers.
- 4. (Currently Amended) The electroluminescent device according to claim 1, wherein the barrier layer comprises including at least one sublayer composed of a silicon compound.
- 5. (Currently Amended) The electroluminescent device according to claim 4, wherein the barrier layer comprises-including a sublayer in contact with the second electrode, the sublayer being composed of silicon oxide.

- 6. (Currently Amended) The electroluminescent device according to claim 4, wherein the barrier layer comprises including a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride.
- 7. (Currently Amended) The electroluminescent device according to claim 4, wherein the barrier layer comprises including a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride oxide.
- 8. (Currently Amended) The electroluminescent device according to claim 1, further comprising:

an insulating layer disposed around the second electrode, the insulating layer being composed of a silicon compound,

wherein-the barrier layer extends extending to the insulating layer.

9. (Currently Amended) The electroluminescent device according to claim 1, further comprising:

a protective layer for covering that covers the barrier layer.

10. (Original) The electroluminescent device according to claim 9, further comprising:

an adhesive layer disposed between the barrier layer and the protective layer.

- 11. (Currently Amended) The electroluminescent device according to claim 10, wherein the adhesive layer comprises including a material that is softer than that of the protective layer.
- 12. (Currently Amended) An electronic apparatus comprising an-the electroluminescent device according to claim 1.
- 13. (Currently Amended) A method for manufacturing an electroluminescent device, comprising the steps of:comprising:

forming a second electrode to-over electroluminescent layers disposed over a first electrode, the second electrode having a surface being composed of an inorganic oxide; and

forming a barrier layer such that at least one portion of the barrier layer comes into direct contact with the second electrode, the barrier layer being composed of an inorganic compound.

- 14. (Currently Amended) The method for manufacturing an electroluminescent device according to claim 13, wherein the second electrode is being formed by vapor phase deposition.
- 15. (Currently Amended) The method for manufacturing an electroluminescent device according to claim 13, wherein the barrier layer is being formed by vapor phase deposition.
- 16. (Currently Amended) The method for manufacturing an electroluminescent device according to any one of claim 13, wherein the second electrode comprises including indium tin oxide or indium zinc oxide.
- 17. (Currently Amended) The method for manufacturing an electroluminescent device according to any one of claim 13, wherein the barrier layer comprises including a silicon compound.
- 18. (Currently Amended) The method for manufacturing an electroluminescent device according to claim 17, wherein the barrier layer has having a sublayer in contact with the second electrode, the sublayer being composed of silicon oxide.
- 19. (Currently Amended) The method for manufacturing an electroluminescent device according to claim 17, wherein the barrier layer has having a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride.

- 20. (Currently Amended) The method for manufacturing an electroluminescent device according to claim 17, wherein the barrier layer has having a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride oxide.
- 21. (Currently Amended) The method for manufacturing an electroluminescent device according to claim 13, wherein the barrier layer extends extending to an insulating layer disposed around the second electrode, the insulating layer being composed of a silicon compound.